

Silicon NPN Power Transistors

2SC3263

DESCRIPTION

- With TO-3PN package
- Complement to type 2SA1294

APPLICATIONS

- Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

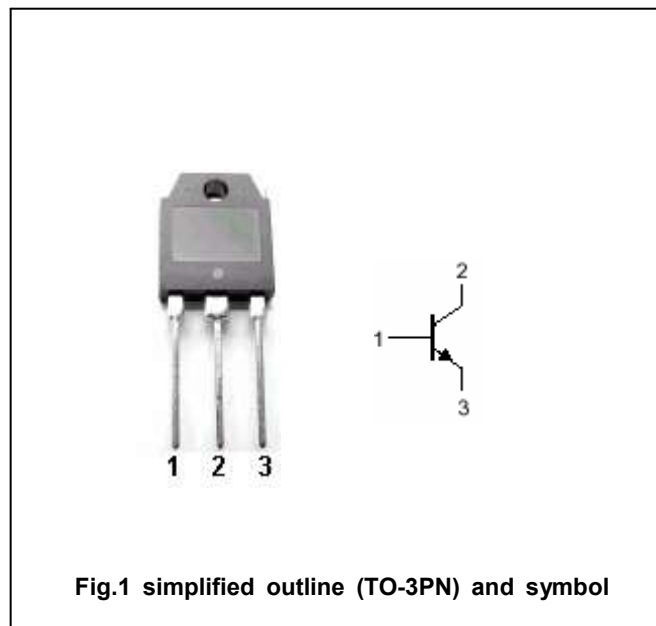


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	230	V
V_{CEO}	Collector-emitter voltage	Open base	230	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
I_B	Base current		4	A
P_C	Collector power dissipation	$T_C = 25\square$	130	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

Silicon NPN Power Transistors

2SC3263**CHARACTERISTICS****T_j=25℃ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0	230			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A I _B =0.5A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =230V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =4V	50		140	
C _{ob}	Output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz		250		pF
f _T	Transition frequency	I _C =2A ; V _{CE} =12V		60		MHz

Switching times

t _{on}	Turn-on time	I _C =5A; R _L =12Ω I _{B1} =- I _{B2} =0.5A V _{CC} =60V		0.3		μs
t _s	Storage time			2.4		μs
t _f	Fall time			0.5		μs

◆ **h_{FE} Classifications**

O	Y
50-100	70-140

Silicon NPN Power Transistors

2SC3263

PACKAGE OUTLINE

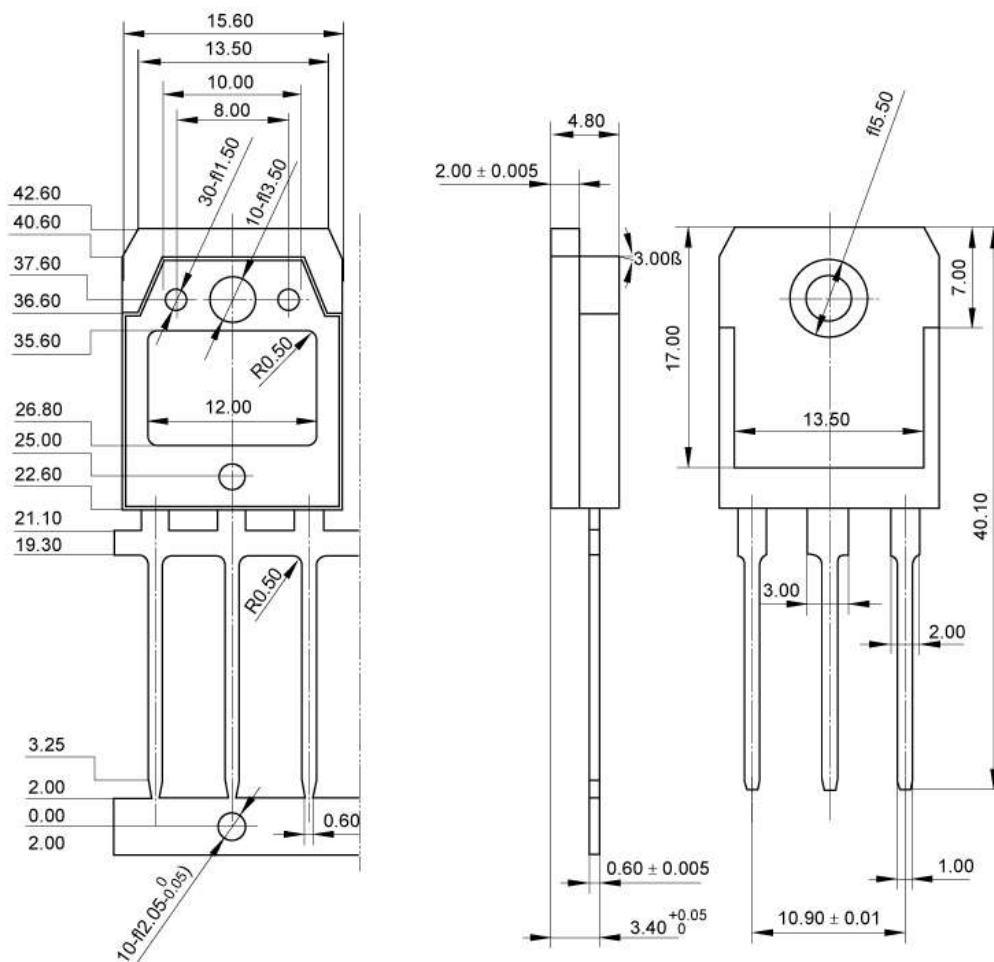


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)

Silicon NPN Power Transistors

2SC3263

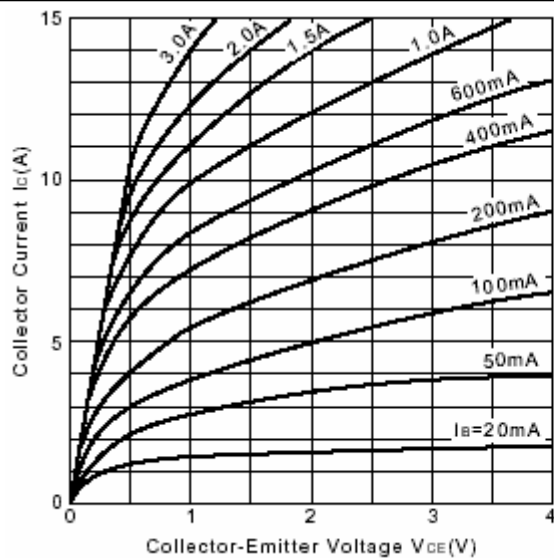


Fig.3 Static Characteristic

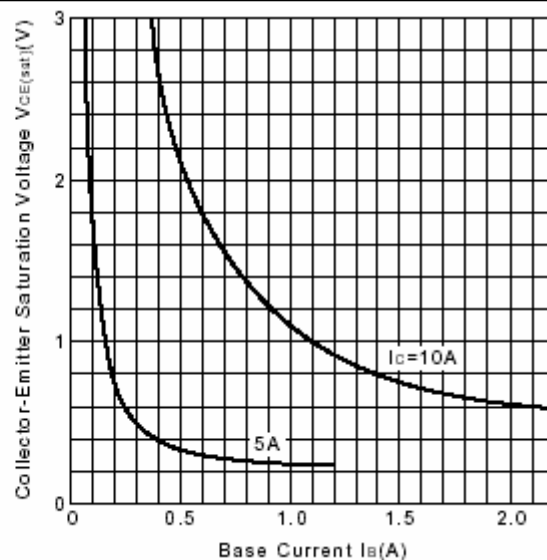
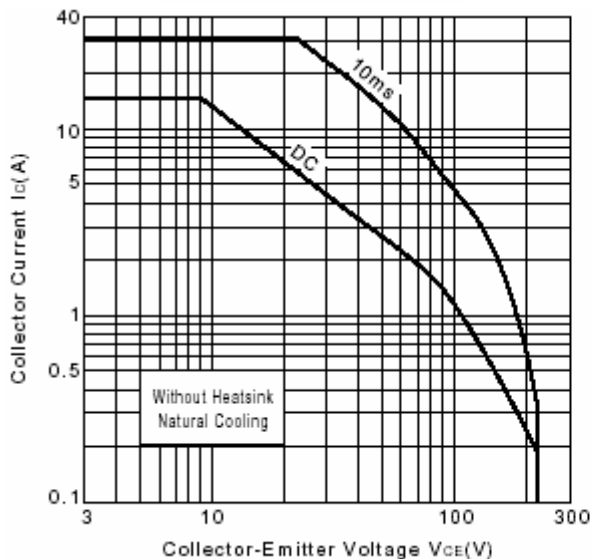
Fig.4 $V_{CE(sat)}-I_B$ 

Fig.5 Safe Operating Area

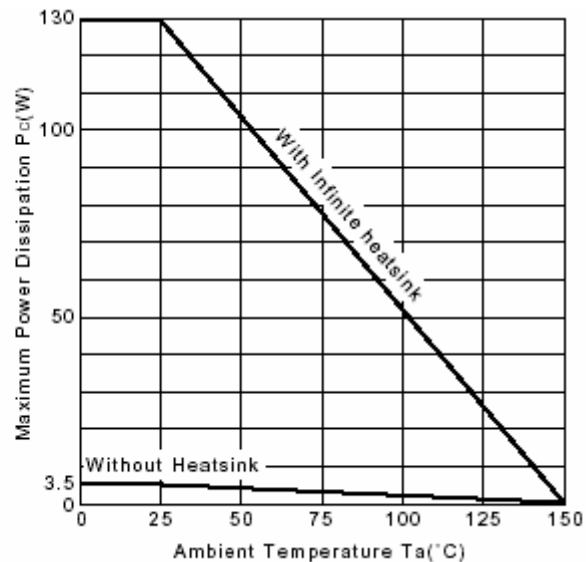


Fig.6 Power Derating

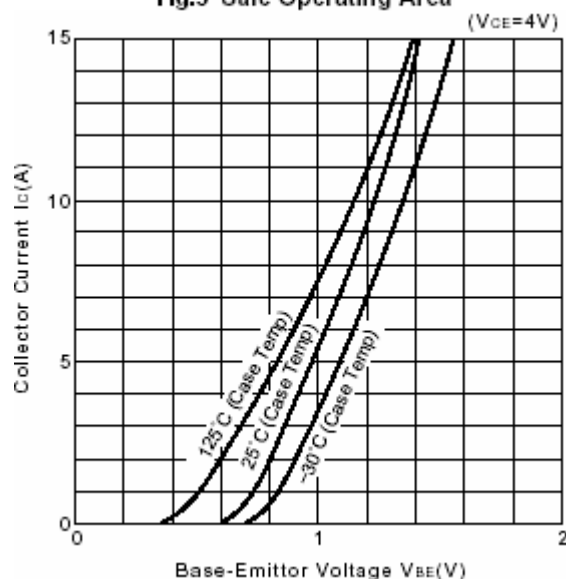
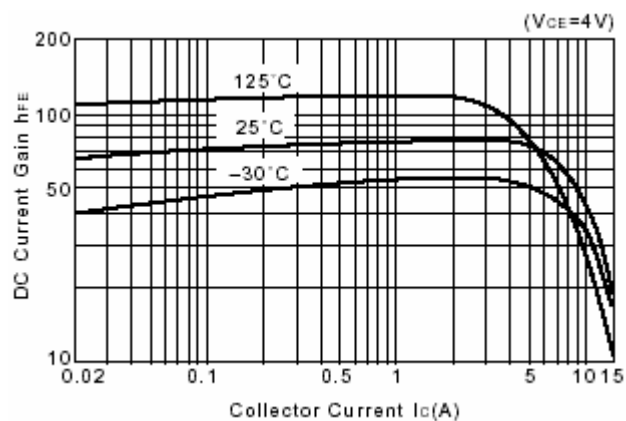
Fig.7 I_C-V_{BE} 

Fig.8 DC current Gain